



STB10NK60Z/-1 - STP10NK60Z/FP STW10NK60Z

N-CHANNEL 600V-0.65Ω-10A - TO220/FP-D²/I²PAK-TO-247
Zener-Protected SuperMESH™ MOSFET

General features

Type	V _{DSS}	R _{DS(on)}	I _D	P _w
STB10NK60Z	600 V	<0.75 Ω	10 A	115
STB10NK60Z-1	600 V	<0.75 Ω	10 A	115
STP10NK60ZFP	600 V	<0.75 Ω	10 A	35
STP10NK60Z	600 V	<0.75 Ω	10 A	115
STW10NK60Z	600 V	<0.75 Ω	10 A	156

- TYPICAL R_{DS(on)} = 0.65 Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- GATE CHARGE MINIMIZED
- VERY LOW INTRINSIC CAPACITANCES
- VERY GOOD MANUFACTURING REPEATABILITY

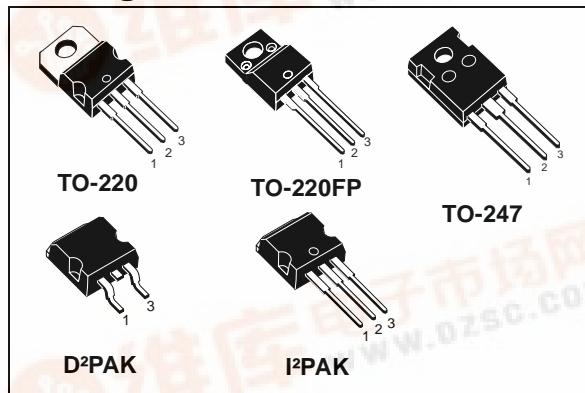
Description

The SuperMESH™ series is obtained through an extreme optimization of ST's well established strip-based PowerMESH™ layout. In addition to pushing on-resistance significantly down, special care is taken to ensure a very good dv/dt capability for the most demanding applications. Such series complements ST full range of high voltage MOSFETs including revolutionary MDmesh™ products.

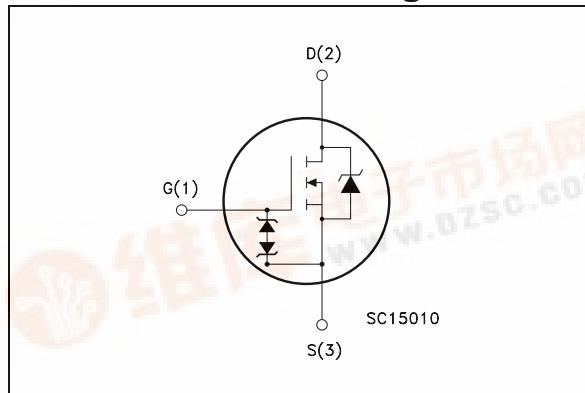
Applications

- HIGH CURRENT, HIGH SPEED SWITCHING
- IDEAL FOR OFF-LINE POWER SUPPLIES, ADAPTOR AND PFC
- LIGHTING

Package



Internal schematic diagram



1 Absolute maximum ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value			Unit
		TO-220/D ² /I ² PAK	TO-220FP	TO-247	
V_{DS}	Drain-Source Voltage ($V_{GS} = 0$)	600			
V_{DGR}	Drain-gate Voltage ($R_{GS} = 20\text{k}\Omega$)	600			
V_{GS}	Gate-Source Voltage	± 30			
I_D	Drain Current (continuous) at $T_C = 25^\circ\text{C}$	10	10 (<i>Note 3</i>)	10	A
I_D	Drain Current (continuous) at $T_C = 100^\circ\text{C}$	5.7	5.7 (<i>Note 3</i>)	5.7	A
I_{DM} <i>Note 2</i>	Drain Current (pulsed)	36	36 (<i>Note 3</i>)	36	A
P_{TOT}	Total Dissipation at $T_C = 25^\circ\text{C}$	115	35	156	W
	Derating Factor	0.92	0.28	1.25	W/ $^\circ\text{C}$
$V_{esd(G-S)}$	G-S ESD (HBM C=100pF, R=1.5k Ω)	4000			V
dv/dt <i>Note 1</i>	Peak Diode Recovery voltage slope	4.5			V/ns
V_{ISO}	Insulation Withstand Volatge (DC)	--	2500	--	V
T_j T_{stg}	Operating Junction Temperature Storage Temperature	-55 to 150			$^\circ\text{C}$

Table 2. Thermal data

		TO-220 I ² PAK	D ² PAK	TO-220FP	TO-247	Unit
$R_{thj-case}$	Thermal Resistance Junction-case Max	1.09		3.6	0.8	$^\circ\text{C/W}$
$R_{thj-pcb}$	Thermal Resistance Junction-pcb Max (when mounted on minimum Footprint)		60			$^\circ\text{C/W}$
$R_{thj-amb}$	Thermal Resistance Junction-amb Max	62.5		50		$^\circ\text{C/W}$
T_I	Maximum Lead Temperature For Soldering Purpose	300				$^\circ\text{C}$

Table 3. Avalanche characteristics

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, repetitive or Not-Repetitive (pulse width limited by T_j max)	9	A
E_{AS}	Single Pulse Avalanche Energy (starting $T_j=25^\circ C$, $I_D=I_{AR}$, $V_{DD}=50V$)	300	mJ
E_{AR}	Repetitive Avalanche Energy (pulse width limited by T_j max)	3.5	mJ

Table 4. Gate-source zener diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV_{GSO}	Gate-Source Breakdown Voltage	$I_{GS}=\pm 1mA$ (Open Drain)	30			V

1.1 PROTECTION FEATURES OF GATE-TO-SOURCE ZENER DIODES

The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

2 Electrical characteristics

($T_{CASE} = 25^\circ\text{C}$ unless otherwise specified)

Table 5. On/Off

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$I_D = 250\mu\text{A}, V_{GS} = 0$	600			V
I_{DSS}	Zero Gate Voltage Drain Current ($V_{GS} = 0$)	$V_{DS} = \text{Max Rating}$,			1 50	μA
I_{GSS}	Gate Body Leakage Current ($V_{DS} = 0$)	$V_{GS} = \pm 15\text{V}, V_{DS} = 0$			± 10	μA
$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	3	3.75	4.5	V
$R_{DS(\text{on})}$	Static Drain-Source On Resistance	$V_{GS} = 10\text{V}, I_D = 20\text{A}$		0.65	0.75	Ω

Table 6. Dynamic

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_f Note 4	Forward Transconductance	$V_{DS} = 15\text{V}, I_D = 4.5\text{A}$		7.8		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{DS} = 25\text{V}, f = 1\text{ MHz}, V_{GS} = 0$		1370 156 37		pF pF pF
C_{oss} eq. Note 5	Equivalent Output Capacitance	$V_{GS} = 0, V_{DS} = 0\text{V to } 480\text{V}$		90		pF
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 480\text{V}, I_D = 8\text{A}$ $V_{GS} = 10\text{V}$ (see Figure 19)		50 10 25	70	nC nC nC

Table 7. Switching on/off

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Delay Time Rise Time	$V_{DD} = 300\text{V}, I_D = 4\text{A},$ $R_G = 4.7\Omega, V_{GS} = 10\text{V}$ (see Figure 20)		20 20		ns ns
$t_{d(off)}$ t_f	Turn-off Delay Time Fall Time	$V_{DD} = 300\text{V}, I_D = 4\text{A},$ $R_G = 4.7\Omega, V_{GS} = 10\text{V}$ (see Figure 20)		55 30		ns ns
$t_{r(Voff)}$ t_f t_c	Off-voltage Rise Time Fall Time Cross-over Time	$V_{DD} = 480\text{V}, I_D = 8\text{A},$ $R_G = 4.7\Omega, V_{GS} = 10\text{V}$ (see Figure 20)		18 18 36		ns ns ns

Table 8. Source drain diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM} ^{Note 2}	Source-drain Current Source-drain Current (pulsed)				10 36	A A
V_{SD} ^{Note 4}	Forward on Voltage	$I_{SD}=10A, V_{GS}=0$			1.6	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD}=8A, di/dt = 100A/\mu s,$ $V_{DD}=40 V, T_j=150^\circ C$		570 4.3 15		ns μC A

(1) $I_{SD} \leq 10A$, $di/dt \leq 200A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$, $T_j \leq T_{JMAX}$

(2) Pulse width limited by safe operating area

(3) Limited only by maximum temperature allowed

(4) Pulsed: pulse duration = 300 μs , duty cycle 1.5%(5) $C_{oss\ eq}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80%

2.1 Typical characteristics

Figure 1. Safe Operating Area for TO-220/D²/I²PAK

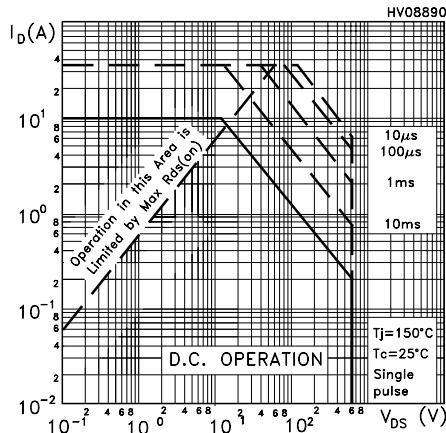


Figure 2. Thermal Impedance for TO-220/D²/I²PAK

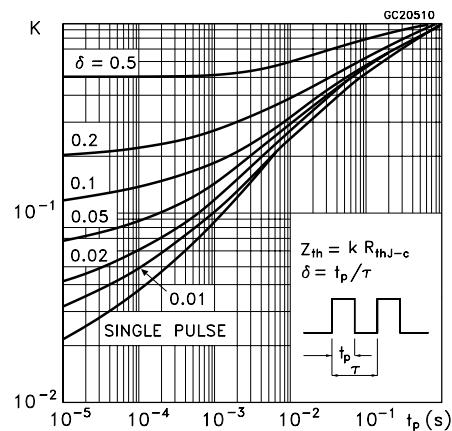


Figure 3. Safe Operating Area for TO-220FP

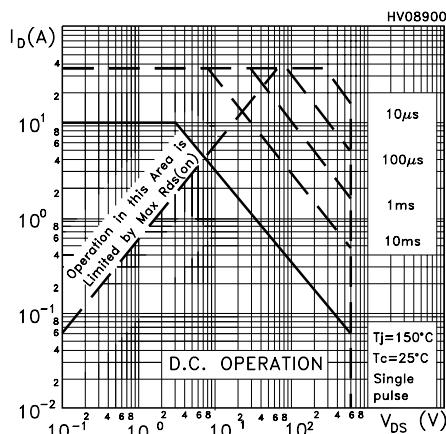


Figure 4. Thermal Impedance for TO-220FP

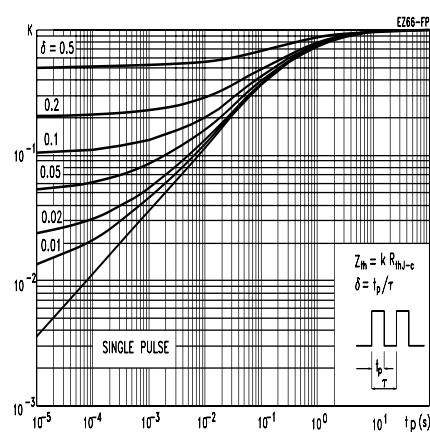


Figure 5. Safe Operating Area for TO-247

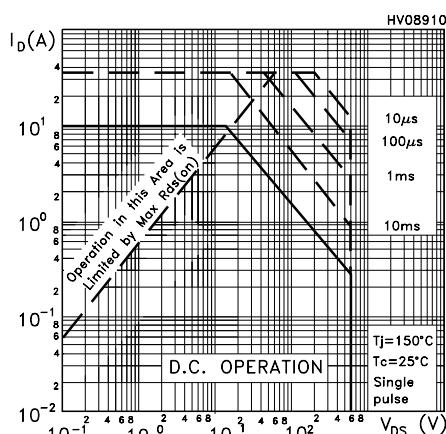


Figure 6. Thermal Impedance for TO-247

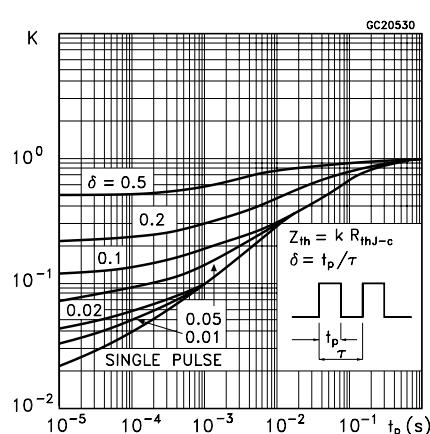


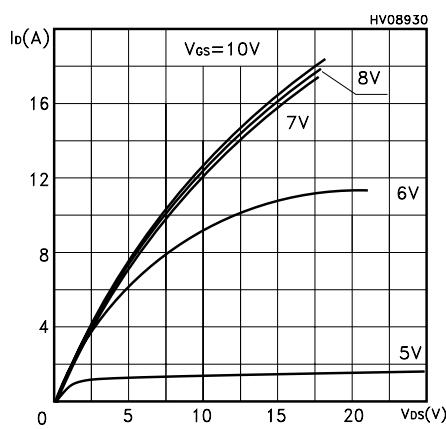
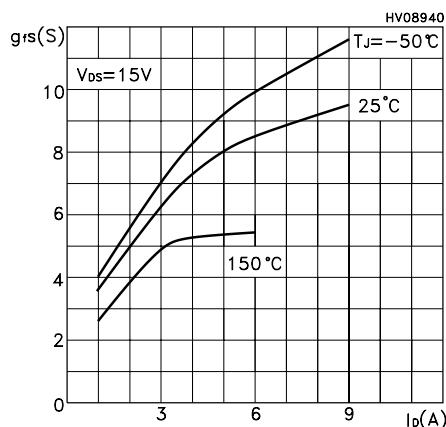
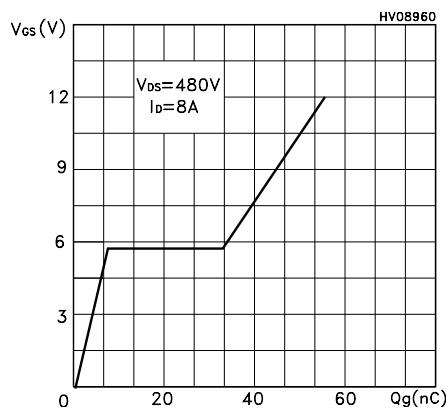
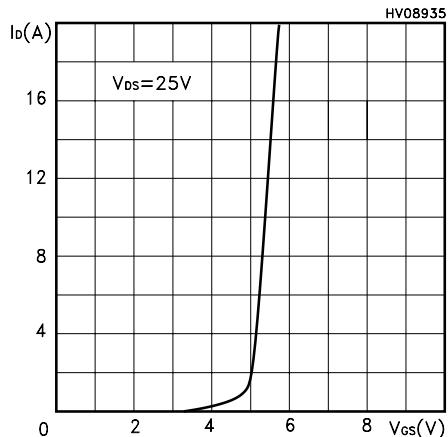
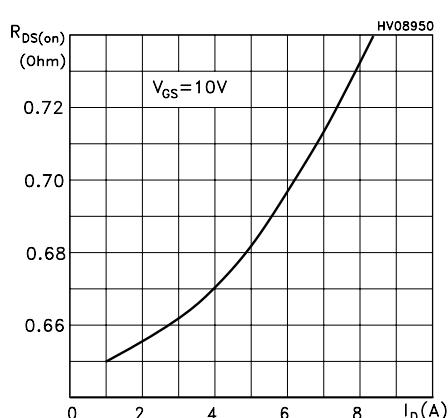
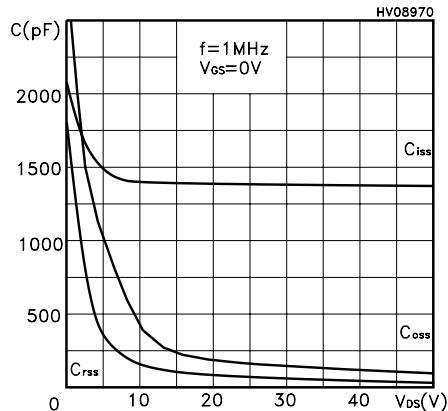
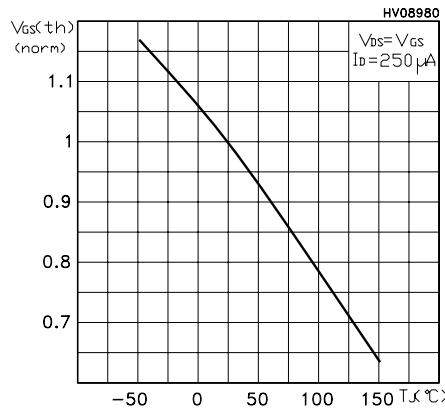
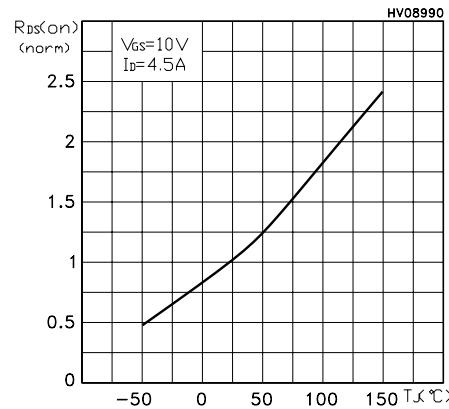
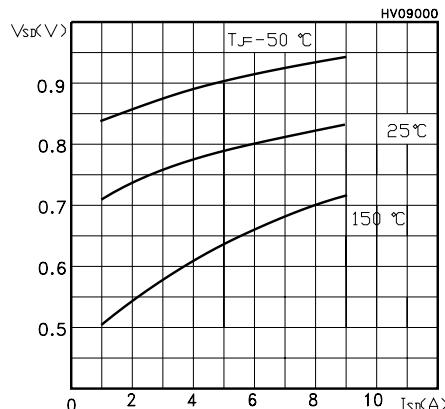
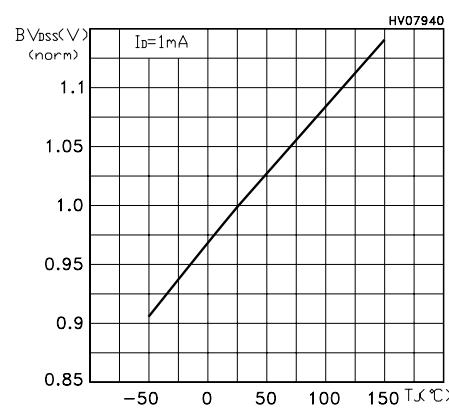
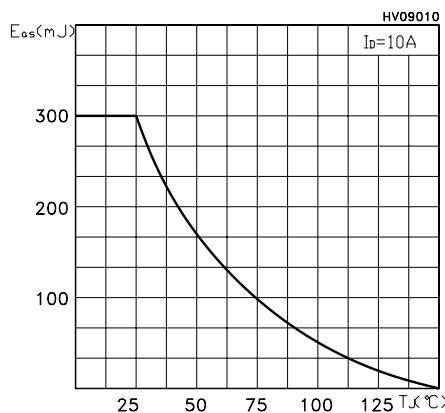
Figure 7. Output Characteristics**Figure 9. Transconductance****Figure 11. Gate Charge vs Gate-Source Voltage****Figure 8. Transfer Characteristics****Figure 10. Static Drain-Source on Resistance****Figure 12. Capacitance Variations**

Figure 13. Normalized Gate Threshold Voltage vs Temperatute**Figure 14. Normalized on Resistance vs Temperature****Figure 15. Source-drain Diode Forward Characteristics****Figure 16. Normalized BVDSS vs Temperature****Figure 17. Maximum Avalanche Energy vs Temperature**

3 Test circuits

Figure 18. Switching Times Test Circuit For Resistive Load

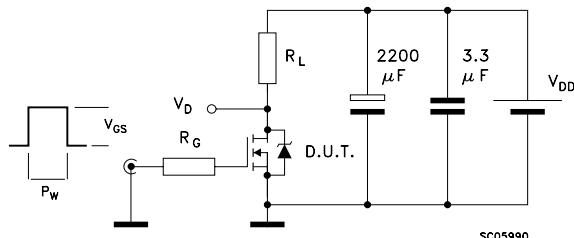
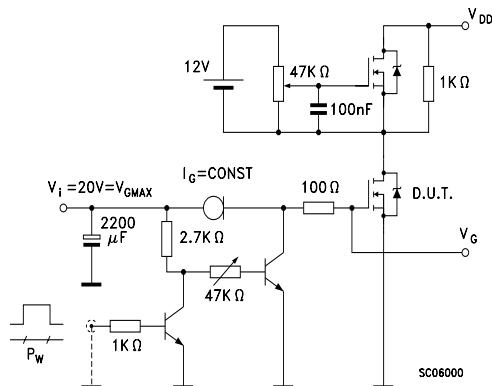
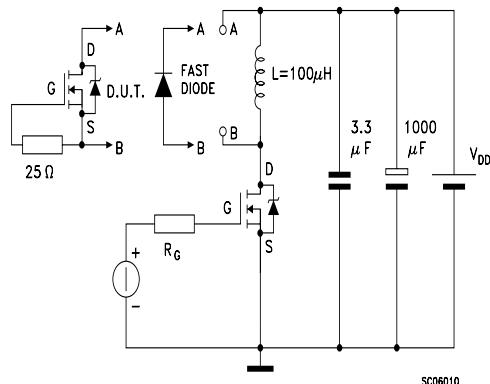


Figure 19. Gate Charge Test Circuit



**Figure 20. Test Circuit For Inductive Load
Switching and Diode Recovery
Times**

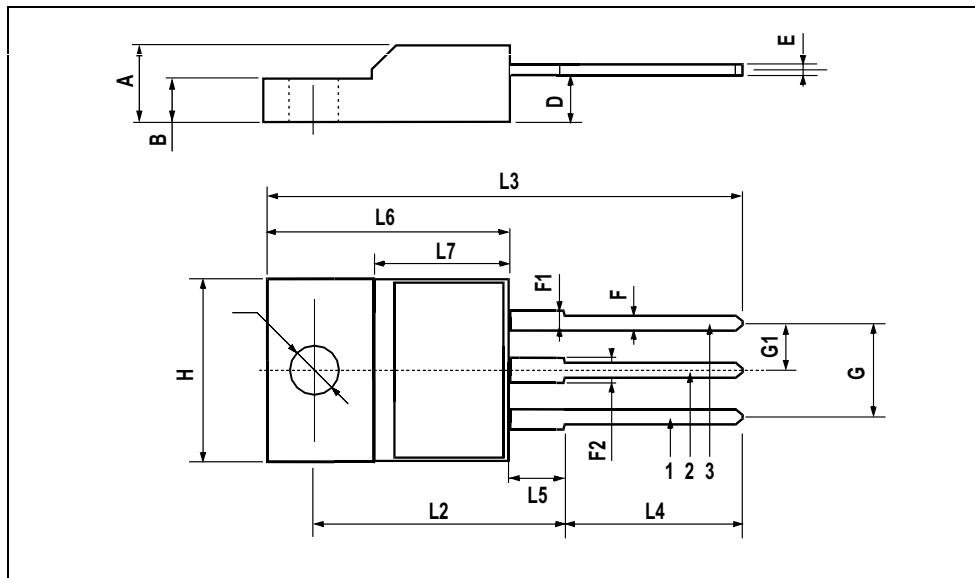


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

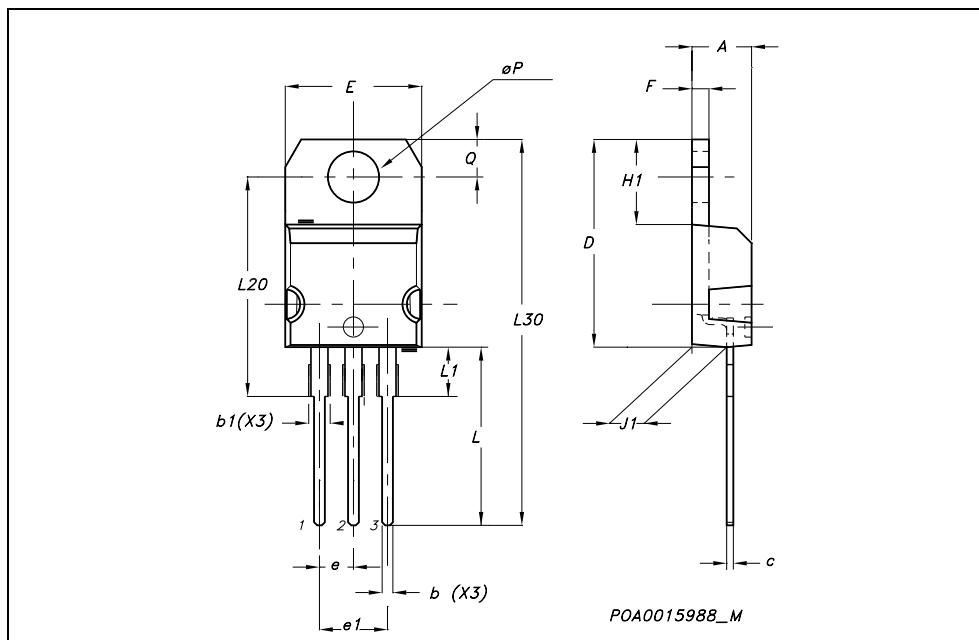
TO-220FP MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	.0385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



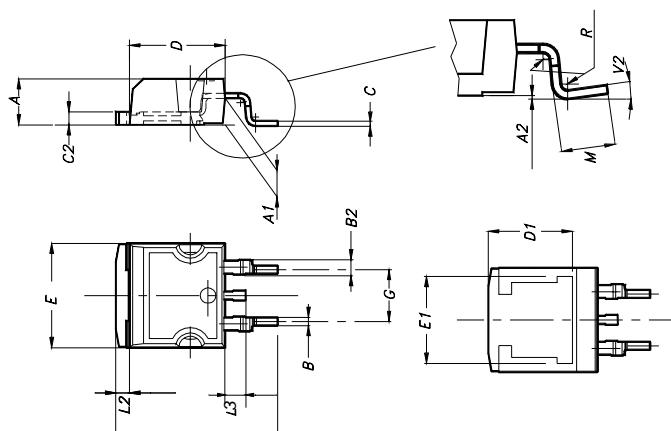
TO-220 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
ϕP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



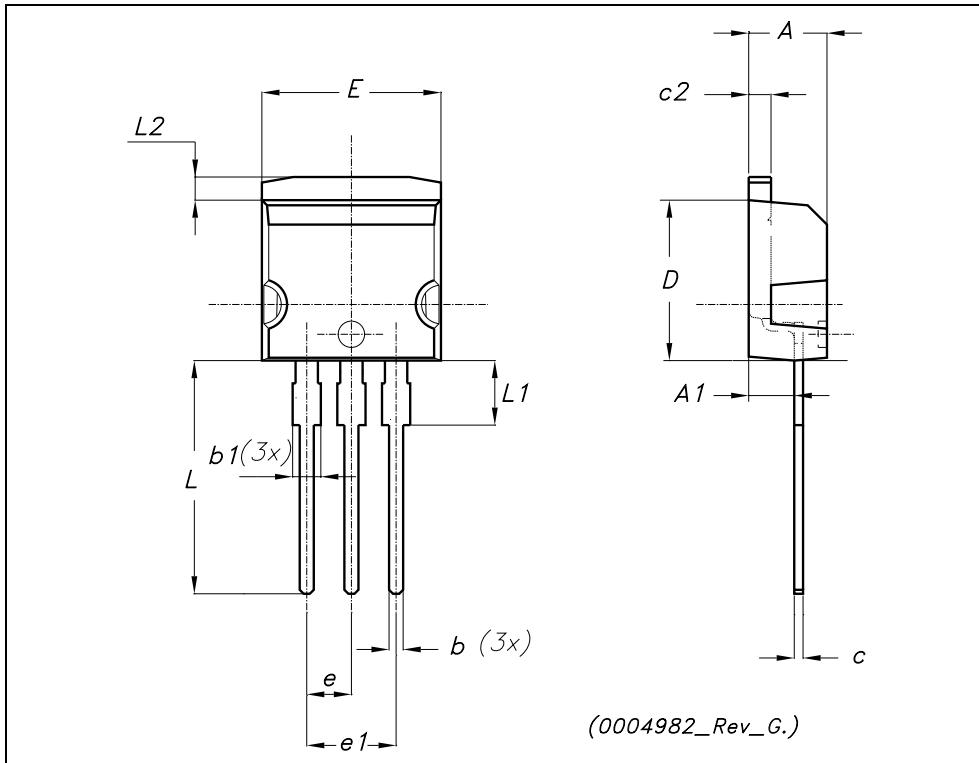
D ² PAK MECHANICAL DATA						
DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		4°			

DIM.	mm.			inch		
MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		4°			



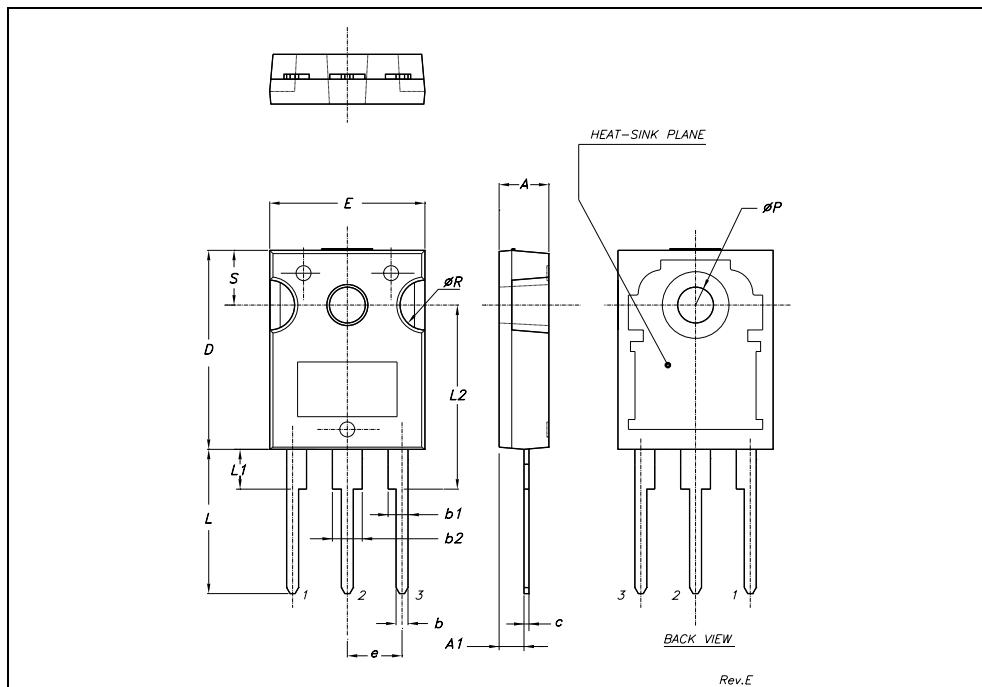
TO-262 (I²PAK) MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
A1	2.40		2.72	0.094		0.107
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.49		0.70	0.019		0.027
c2	1.23		1.32	0.048		0.052
D	8.95		9.35	0.352		0.368
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
E	10		10.40	0.393		0.410
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L2	1.27		1.40	0.050		0.055



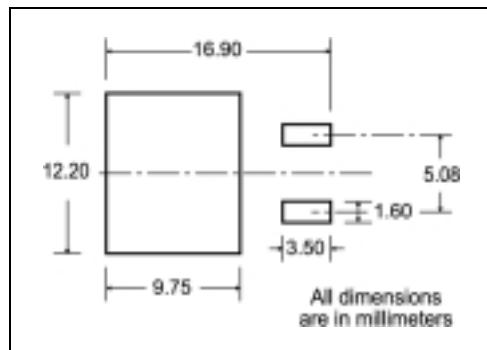
TO-247 MECHANICAL DATA						
DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.

A	4.85		5.15	0.19		0.20
A1	2.20		2.60	0.086		0.102
b	1.0		1.40	0.039		0.055
b1	2.0		2.40	0.079		0.094
b2	3.0		3.40	0.118		0.134
c	0.40		0.80	0.015		0.03
D	19.85		20.15	0.781		0.793
E	15.45		15.75	0.608		0.620
e		5.45			0.214	
L	14.20		14.80	0.560		0.582
L1	3.70		4.30	0.14		0.17
L2		18.50			0.728	
øP	3.55		3.65	0.140		0.143
øR	4.50		5.50	0.177		0.216
S		5.50			0.216	



5 Packing mechanical data

D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT

REEL MECHANICAL DATA				
DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A	330		12.992	
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

BASE QTY		BULK QTY	
1000		1000	
<p>Diagram illustrating reel dimensions and tape handling. It shows the top cover tape, cavity dimensions (R1, R2, R3, R4, R5, R6), cumulative tolerance (+/- 0.2 mm), center line of cavity, user direction of feed, and bending radius (R min.).</p>			

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956

* on sales type

6 Order codes

Sales Type	Marking	Package	Packaging
STB10NK60Z-1	B10NK60Z-1	I ² PAK	TUBE
STB10NK60ZT4	B10NK60Z	D ² PAK	TAPE & REEL
STP10NK60ZFP	P10NK60ZFP	TO-220FP	TUBE
STP10NK60Z	P10NK60Z	TO-220	TUBE
STW10NK60Z	W10NK60Z	TO-247	TUBE

7 Revision History

Date	Revision	Changes
26-Jul-2005	2	Inserted Ecopack indication

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